IN THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application

Listing of Claims:

1. (Currently Amended) A semiconductor light-emitting device comprising:

a substrate made of group III-V nitride semiconductor;

a first n-type semiconductor layer containing indium and formed over a main surface of the substrate; and

a light-emitting layer formed ~~between~~ over the first n-type semiconductor layer ~~and the substrate~~.

2. (Original) The device of claim 1,

wherein the substrate is made of gallium nitride.

3. (Original) The device of claim 1,

wherein the main surface of the substrate is polished.

4. (Original) The device of claim 3,

wherein the main surface of the substrate is etched.

5. (Original) The device of claim 3,

wherein the main surface of the substrate is planarized.

6. (Original) The device of claim 1,

wherein the light-emitting layer has a multiple quantum well structure formed by alternately stacking a quantum well layer and a barrier layer, and

the quantum well layer has a thickness of 1 to 2.5 nm inclusive.

7. (Currently Amended) The device of claim 1,

wherein the first n-type semiconductor layer is made of a compound whose general

formula is represented by $In_aAl_bGa_{1-a-b}N$ ~~$(0<a<1, 0\leq b<1, a+b\leq 1)$~~ $(0<a\leq 1, 0\leq b<1, a+b\leq 1)$.

8. (Original) The device of claim 7,

wherein the aluminum content of the first n-type semiconductor layer is 3% or lower.

9. (Original) The device of claim 1,

wherein the first n-type semiconductor layer has a thickness of 10 nm to 1 μm inclusive.

10. (Original) The device of claim 1, further comprising a second n-type semiconductor layer formed between the substrate and the first n-type semiconductor layer.

11. (Original) The device of claim 10,

wherein the second n-type semiconductor layer is made of a compound whose general formula is represented by $In_cAl_dGa_{1-c-d}N$ $(0\leq c<1, 0\leq d<1, c+d<1)$.

12. (Original) The device of claim 11,

wherein the second n-type semiconductor layer is an n-type contact layer.

13. (Original) The device of claim 8, further comprising a third n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer.

14. (Original) The device of claim 13,

wherein the third n-type semiconductor layer is an n-type contact layer.

15. (Original) The device of claim 1, further comprising a fourth n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer.

16. (Original) The device of claim 15,

wherein the fourth n-type semiconductor layer is made of a compound whose general formula is represented by $Al_eGa_{1-e}N$ $(0\leq e<1)$.

17. (Original) The device of claim 16,

wherein the fourth n-type semiconductor layer is a cladding layer.

18. (Original) The device of claim 17,

wherein the cladding layer has a thickness of 5 to 200 nm inclusive.

19. (Original) The device of claim 1, further comprising:

an n-type contact layer which is formed between the substrate and the light-emitting layer and a portion of which is exposed;

an n-side electrode formed on the exposed portion of the n-type contact layer;

an n-type cladding layer formed between the first n-type semiconductor layer and the light-emitting layer;

a p-type semiconductor layer formed on the light-emitting layer; and

a p-side electrode formed over the p-type semiconductor layer,

wherein the device is mounted with an element formation surface thereof facing a submount for mounting.

20. (Currently Amended) A illuminating device comprising the multiple semiconductor light-emitting devices of ~~claims 1-19~~ claim 1.